

## **15.1.0 ANALOGUE ELECTRONICS I**

### **15.1.01 Introduction**

Analogue electronics is a study that deals with electronic systems with a continuously variable signal. This module unit is intended to impart knowledge, skills and attitudes required to enable the trainee understand the principles of operations of various electrical circuits, equipment and devices in the industries. This unit forms a foundation for Analogue Electronics II in Module II.

### **15.1.02 General Objectives**

At the end of the module unit, the trainee should be able to:

- a) Understand the operation of analogue electronic devices
- b) Apply analogue electronic components in the construction of power supply units and other electronic devices
- c) Observe safety when using analogue electronic components and devices

### **15.1.1 Module Unit Summary and Time Allocation**

#### **Analogue Electronics I**

| <b>Code</b> | <b>Module Unit</b>      | <b>Content</b>  | <b>Time Hrs</b> |
|-------------|-------------------------|---|-----------------|
| 15.1.1      | Atomic Theory of matter | <ul style="list-style-type: none"><li>• Atomic structure</li><li>• Energy levels</li></ul>  | 8               |
| 15.1.2      | Thermionic Emission     | <ul style="list-style-type: none"><li>• Principles of the CRT</li><li>• Advantages and limitations of valves</li><li>• Motions of electrons</li><li>• Principles of the CRO</li><li>• Applications of thermionic emission</li></ul> | 10              |
| 15.1.3      | Semi conductor theory   | <ul style="list-style-type: none"><li>• Intrinsic semi conductor.</li><li>• Effect of temperature on intrinsic semiconductor</li><li>• Doping p and n types</li><li>• Formation of extrinsic</li></ul>                              | 8               |

|                   |                              |   |           |
|-------------------|------------------------------|---|-----------|
|                   |                              | semiconductor   |           |
| 15.1.4            | Semi-conductor diodes        | <ul style="list-style-type: none"> <li>• PN junction diode</li> <li>• Forward and reverse bias of pn junction diodes</li> <li>• Applications of pn junction diodes</li> </ul>   | 10        |
| 15.1.5            | Bipolar Junction Transistors | <ul style="list-style-type: none"> <li>• Operation of NPN and PNP</li> <li>• Characteristics</li> <li>• Biasing methods</li> <li>• Determination of gains using Dc/ac load-lines</li> </ul>                                   | 8         |
| 15.1.6            | Field Effect Transistor      | <ul style="list-style-type: none"> <li>• Operation of field effect transistors</li> <li>• Biasing methods</li> <li>• Determination of gains using dc/ac load-lines</li> </ul>   | 10        |
| 15.1.7            | Power supply units           | <ul style="list-style-type: none"> <li>• Transformation</li> <li>• Rectification</li> <li>• Filtering</li> <li>• Stabilization</li> <li>• Regulation</li> <li>• Voltage multiplication</li> <li>• Power conversion</li> </ul> | 12        |
| <b>Total Time</b> |                              |   | <b>66</b> |

### 15.1.1 ATOMIC THEORY OF MATTER

#### Theory

#### 15.1.1T0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- a) explain atomic structure
- b) explain energy level of an Atom

#### *Content*

#### 15.1.1T1 Explanation of atomic structure

- i) The atom
- ii) Rutherford's atomic model
- iii) Plank's quantum Theory of radiation
- iv) Bohr's model

#### 15.1.1T2 Explain the energy levels

- i) Energy level diagram
- ii) Collision of electrons and atoms
- iii) Photons of light
- iv) Spectral lines
- v) Photo ionization
- vi) Conduction band
- vii) Valence band
- viii) Forbidden gap

### 15.1.2 THERMIONIC EMISSION

#### Theory

#### 15.1.2T0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- a) explain principles of thermionic emission

- b) state the advantages and limitations of valves in electronic industry
- c) explain the motion of electrons in a magnetic and electrostatic field
- d) describe the construction and operation of a Cathode Ray Tube (CRT)
- e) describe the construction and operation of a Cathode Ray Oscilloscope (CRO)
- f) explain the application of thermionic emission

#### *Content*

#### 15.1.2T1 Principles of thermionic emission

- i) Work function
- ii) Space charge
- iii) Direct and indirect heating
- iv) Electron emitting materials

#### 15.1.2T2 Applications and limitations of valves

#### 15.1.2T3 Motion of electrons in magnetic and electrostatic fields

- i) Force
- ii) Deflection in transverse field
- iii) Magnetic field deflection
- iv) Electrostatic field deflection
- v) Electron velocity
- vi) Deflection of an electron beam

#### 15.1.2T4 Cathode Ray Tube

- i) Construction
- ii) Operation
- iii) Application

#### 15.1.2T5 Cathode Ray Oscilloscope

- i) Describe the construction by block diagram
  - ii) Describe the operation
- 15.1.2T6 Applications

### Practice

#### 15.1.2P0 *Specific Objectives*

By the end of the sub module unit, the trainee should be able to:

- a) operate a cathode-ray oscilloscope (CRO)
- b) take measurements using a CRO

### Content

15.1.2P1 Operating a CRO

15.1.2P2 Taking measurements using a CRO

15.1.2C Competence

The trainee should have the ability to:

- i) Operate a CRO
- ii) Take measurements using a CRO

### Learning Resources

- i) Cathode-ray oscilloscope
- ii) Signal generators
- iii) Probes

## 15.1.3 SEMI CONDUCTOR THEORY

### Theory

#### 15.1.3T0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- a) explain intrinsic semiconductor

- b) explain effect of temperature on intrinsic semiconductor
- c) describe doping
- d) describe formation of extrinsic semiconductor

### Content

15.1.3T1 Bond in Intrinsic semi conductors

- i) Ge Si
- ii) Covalent bonding

15.1.3T2 Temperature on intrinsic semi conductor materials

15.1.3T3 Doping

15.1.3T4 Formation of extrinsic semi conductor

- iv) p type
- v) n type

### Practice

#### 15.1.3P0 *Specific Objectives*

By the end of the sub module unit, the trainee should be able to verify the effect of temperature on a diode performance

### Content

15.1.3P1 Verification of the effect of temperature on diode

#### 15.1.3C Competence

The trainee should have the ability to:

- i) Verify the effect of temperature on diodes
- ii) Use a diode in electronic circuits

### Suggested teaching/Learning Activities

- Demonstration

- Note taking
- Observation
- Practical exercise

#### *Suggested teaching/Learning*

#### *Resources*

- i) Various types of diodes
- ii) Electronic tool kit
- iii) Power supply

#### *Suggested Evaluation Methods*

- Oral tests
- Timed written tests
- Assignments
- Timed practical tests

### **15.1.4 SEMICONDUCTOR DIODE**

#### **Theory**

#### **15.1.4T0 Specific Objectives**

By the end of the sub module unit the trainee should able to:

- a) **describe** formation of PN junction
- b) explain forward and reverse bias of PN junction
- c) explain applications of semiconductor diodes

#### *Content*

#### **15.1.4T1 Formation of an PN junction diode.**

- i) Diffusion
- ii) Depletion layer
- iii) Barrier potential

#### **15.1.4T2 Forward and reverse mode of operation of PN junction diode.**

- i) Drift
- ii) Forward characteristics
- iii) Reverse characteristics
- iv) Zener Avalanche effect

#### **15.1.4T3 Application of semiconductor diodes**

- i) Power diodes
- ii) signal diodes

#### **Practice**

#### **15.1.4P0 Specific Objectives**

By the end of the sub module unit, the trainee should be able to:

- a) identify the diode terminals
- b) determine diode characteristics

#### *Content*

#### **15.1.4P1 Identifying diode terminals**

#### **15.1.4P2 Determining diode characteristics**

#### **15.1.4C Competence**

The trainee should have the ability to:

- i) Identify diode terminals
- ii) Determine diode characteristics

#### *Suggested teaching/Learning Activities*

- Demonstration
- Note taking
- Observation
- Practical exercise

#### *Learning Resources*

- i) Assorted semi conductor diodes
- ii) DC power supply
- iii) Multimeters
- iv) Graph paper
- v) X-ray plotter

#### *Suggested Evaluation Methods*

- Oral tests
- Timed written tests
- Assignments
- Timed practical tests

### 15.1.5 BIPOLAR JUNCTION TRANSISTORS

#### Theory

#### 15.1.5T0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- a) describe the construction and operation of a Bipolar Junction Transistors (BJT)
- b) explain the characteristics of Bipolar Junction Transistor
- c) describe the biasing methods
- d) determine gains using DC load lines

#### *Content*

#### 15.1.5T1 Construction and operation of BJTs

- i) NPN
- ii) PNP

#### 15.1.5T2 Static characteristics of BJTs

- i) Input
- ii) Output
- iii) Transfer

#### 15.1.5T3 Transistor biasing methods

- i) Base bias
- ii) Emitter bias
- iii) Collector base feedback bias
- iv) Potential divider bias

#### 15.1.5T4 DC load-lines

DC load-line

- i) Gain estimates
- ii) Current, voltage and power gain
- iii) Maximum power curve.

#### Practice

#### 15.1.5P0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- a) identify the type of transistors
- b) determine static transistor characteristics
- c) bias a transistor amplifier
- d) construct dc loadlines

#### *Content*

#### 15.1.5P1 Identifying types of transistors

#### 15.1.5P2 Determining static characteristics of transistors

#### 15.1.5P3 Biasing transistor amplifier

#### 15.1.5P4 Constructing dc loadlines

### 15.1. C Competence

The trainee should have the ability to:

- i) Construct a single stage transistor amplifier
- ii) Test a single stage transistor amplifier

#### *Suggested teaching/Learning Activities*

- Illustration
- Demonstration
- Note taking

#### *Learning Resources*

- i) Power supplies
- ii) Assorted transistors
- iii) Breadboard

- Oral tests
- Timed written tests
- Assignments
- Timed practical tests

### 15.1.5 BIPOLAR JUNCTION TRANSISTORS

#### Theory

#### 15.1.5T0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- describe the construction and operation of a Bipolar Junction Transistors (BJT)
- explain the characteristics of Bipolar Junction Transistor
- describe the biasing methods
- determine gains using DC load lines

#### *Content*

#### 15.1.5T1 Construction and operation of BJTs

- NPN
- PNP

#### 15.1.5T2 Static characteristics of BJTs

- Input
- Output
- Transfer

#### 15.1.5T3 Transistor biasing methods

- Base bias
- Emitter bias
- Collector base feedback bias
- Potential divider bias

#### 15.1.5T4 DC load-lines

DC load-line

- Gain estimates
- Current, voltage and power gain
- Maximum power curve.

#### Practice

#### 15.1.5P0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- identify the type of transistors
- determine static transistor characteristics
- bias a transistor amplifier
- construct dc loadlines

#### *Content*

#### 15.1.5P1 Identifying types of transistors

#### 15.1.5P2 Determining static characteristics of transistors

#### 15.1.5P3 Biasing transistor amplifier

#### 15.1.5P4 Constructing dc loadlines

### 15.1. C Competence

The trainee should have the ability to:

- Construct a single stage transistor amplifier
- Test a single stage transistor amplifier

#### *Suggested teaching/Learning Activities*

- Illustration
- Demonstration
- Note taking

#### *Learning Resources*

- Power supplies
- Assorted transistors
- Breadboard

- iv) Connecting leads
- v) Multimeters
- vi) X-Y plotter
- vii) Assorted resistors
- Observation
- Practical exercise
- Calculations
- Project work
- Role play
- Visits to industries

#### *Suggested Evaluation Methods*

- Oral tests
- Timed written tests
- Assignments
- Timed practical tests

### **15.1.6 FIELD EFFECT TRANSISTORS**

#### **Theory**

- 15.1.6T0 *Specific Objectives*  
By the end of the sub module unit the trainee should be able to:
- a) explain the characteristics of field effect transistor
  - b) describe the biasing methods
  - c) determine gains using dc and ac load-lines

#### *Content*

- 15.1.6T1 Construction and operation of FETs
- i) Static characteristics of fets
  - ii) Jfets
  - iii) Mosfets
  - iv) Input
  - v) Output
  - vi) Transfer
- 15.1.6T2 FETs biasing methods
- i) Gate bias

- ii) Source bias
  - iii) Drain base feedback bias
  - iv) Potential divider bias
- 15.1.6T3 DC load-lines
- i) DC Load-line
  - ii) Estimation gain (current, voltage and power)
  - iii) Maximum power curve.

#### **Practice**

- 15.1.6P0 *Specific Objectives*  
By the end of the sub module unit the trainee should be able to:
- a) identify the types of FETs
  - b) determine static FET characteristics
  - c) bias a FET
  - d) construct dc loadline

#### *Content*

- 15.1.6P1 Identifying types of FETs
- 15.1.6P2 Determination static characteristic of FETs
- 15.1.6P3 Biasing a FET amplifier
- 15.1.6P4 Construction of dc loadlines

#### **15.1.6C Competence**

The trainee should have the ability to:

- i) Construct a single stage FET amplifier
- ii) Test a single stage FET amplifier

#### *Suggested teaching/Learning Activities*

- Demonstration
- Note taking
- Observation
- Practical exercise



*Suggested teaching/Learning Resources*

- i) Field effect transistors
- ii) Power supply
- iii) Electronic tools
- iv) Electrical measuring instruments

*Suggested Evaluation Methods*

- Oral tests
- Timed written tests
- Assignments
- Timed practical tests

## 15.1.7 POWER SUPPLIES

### Theory

#### 15.1.7T1 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- a) describe block diagram of power supply
- b) explain principles rectification
- c) explain smoothing and filtering
- d) explain power regulation/stabilizer methods
- e) describe voltage multiplier methods
- f) describe methods of power conversion

#### *Content*

#### 15.1.7T1 Description of the block diagram of power supply

- i) Transformation
- ii) Rectification
- iii) Filters
- iv) Regulator

#### 15.1.7T2 Explanation of principles rectification

- i) Half wave
- ii) Full wave bi-phase

#### iii) Bridge

#### 15.1.7T3 Explanation

filtration/smoothing

- i) Capacitor filter
- ii) Inductive filtering

#### 15.1.7T4 Explanation power regulation/stabilizer methods

- i) Zener diode regulator
- ii) Linear regulators
- iii) Switched regulators

#### 15.1.7T5 Description of voltage multiplier methods

- i) Doubler
- ii) Tripler
- iii) Cockroft walton

#### 15.1.7T6 Description of methods of power conversion

- i) Dc to ac
- ii) Dc to dc

### Practice

#### 15.1.7P0 *Specific Objectives*

By the end of the sub module unit the trainee should be able to:

- a) Construct a power supply unit
- b) Test a power supply unit

#### *Content*

#### 15.1.7P1 Construction of power supply units

#### 15.1.7P2 Testing a power supply unit

## 15.1.7C Competence

The trainee should have the ability to: construct and test a power supply unit

### *Suggested teaching/Learning Activities*

- Demonstration
- Note taking
- Observation

- Practical exercise

*Teaching/Learning Resources*

- i) Step-down transformer
- ii) Rectifier diodes
- iii) Smoothing capacitor
- iv) Zener diode regulations
- v) Transistor regulations
- vi) IC regulators
- vii) Potentiometers
- viii) Assorted resistors

- ix) Multimeters
- x) CRP
- xi) RF bypass capacitors

*Suggested Evaluation Methods*

- Oral tests
- Timed written tests
- Assignments
- Timed practical tests
- Project